

● General Description

The AGM304A-B combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

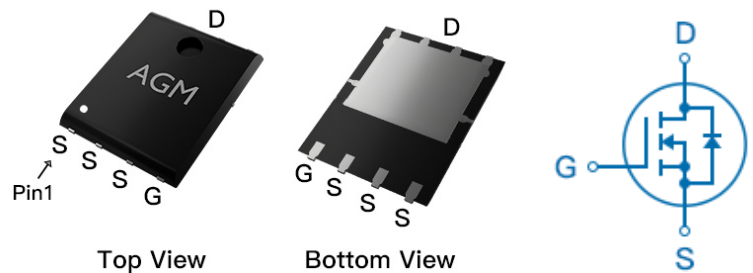
● Application

- Electronic Ballast
- Electronic Transformer
- Switch Mode Power Supply

Product Summary

BVDSS	RDSON	ID
35V	3.3mΩ	75A

PDFN5*6 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM304A	AGM304A-B	PDFN5*6	330mm	12mm	3000

Table 1. Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	35	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	75	A
	Drain Current-Continuous(Tc=100°C)	50	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	300	A
PD	Maximum Power Dissipation(Tc=25°C)	23	w
	Maximum Power Dissipation(Tc=100°C)	9.3	w
EAS	Avalanche energy (Note 3)	81	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	--	20	°C/W
RθJC	Thermal Resistance Junction-Case ¹	--	5.4	°C/W

Table 3. Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	35	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=30V, VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	1.2	1.5	2.2	V
gFS	Forward Transconductance	VDS=5V, ID=15A	--	17	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=20A	--	3.3	4.8	mΩ
		VGS=4.5V, ID=15A	--	4.7	6.4	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=15V, VGS=0V, F=1MHZ	--	860	--	pF
Coss	Output Capacitance		--	430	--	pF
Crss	Reverse Transfer Capacitance		--	56	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V, f=1.0MHz	0.7	1.55	2.3	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V, VDS=15V, RL=0.75 , RGEN=3	--	8.9	--	nS
tr	Turn-on Rise Time		--	73.9	--	nS
td(off)	Turn-Off Delay Time		--	17.7	--	nS
tf	Turn-Off Fall Time		--	81	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=15V, ID=20A	--	17	--	nC
Qgs	Gate-Source Charge		--	3.8	--	nC
Qgd	Gate-Drain Charge		--	3.2	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	75	A
VSD	Forward on Voltage	VGS=0V, ISD=20A	--	--	1.2	V
trr	Reverse Recovery Time	IF=20A , dI/dt=100A/μs , TJ=25°C	--	14	--	ns
Qrr	Reverse Recovery Charge		--	3	--	nc

Notes 1. The maximum current rating is package limited.

Notes 2. Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3. EAS condition: T_J=25°C, VDD=20V, Vgs=10V, ID=18A, L=0.5mH, RG=25ohm

TYPICAL ELECTRICAL AND THERMAL CHARACTERIS

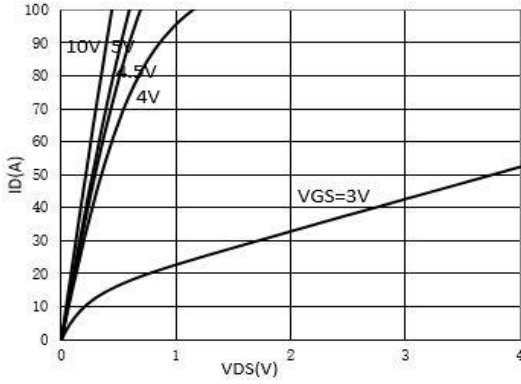


Figure 1: On-Region Characteristics (Note E)

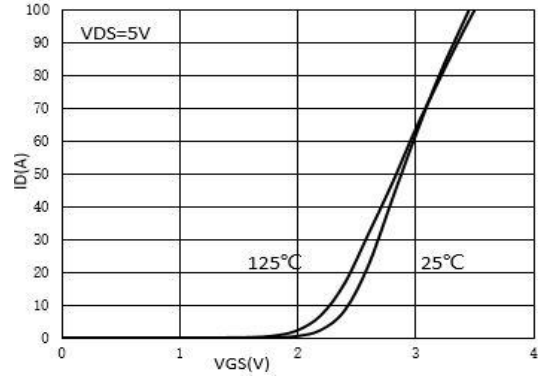


Figure 2 Transfer Characteristics (Note E)

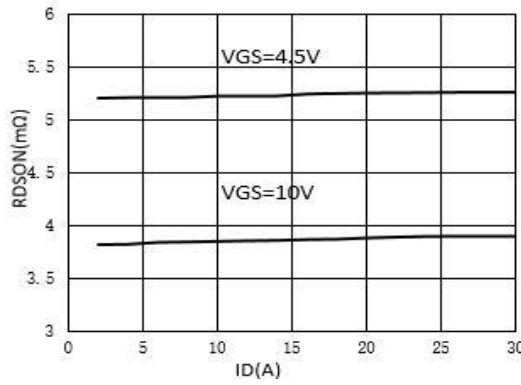


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

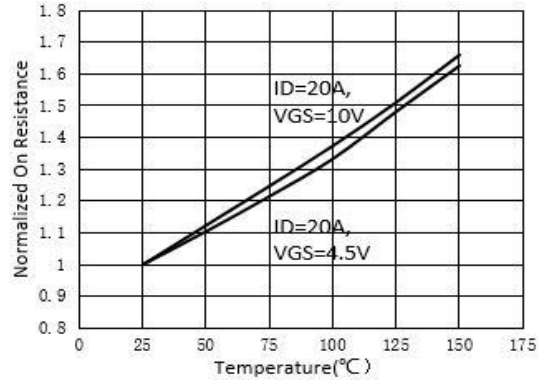


Figure 4: On-Resistance vs. Junction Temperature (Note E)

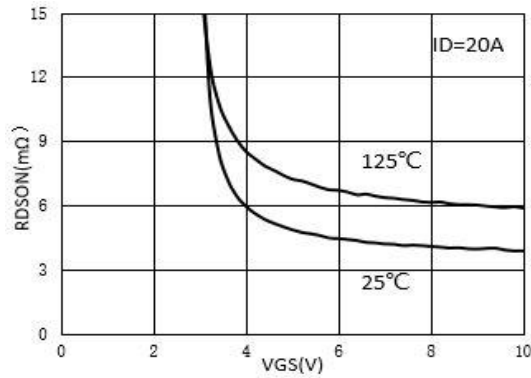


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

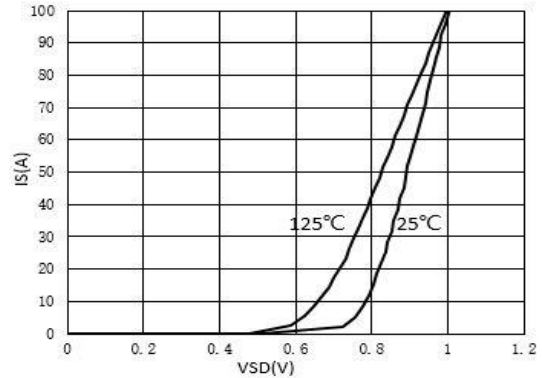


Figure 6: Body-Diode Characteristics (Note E)

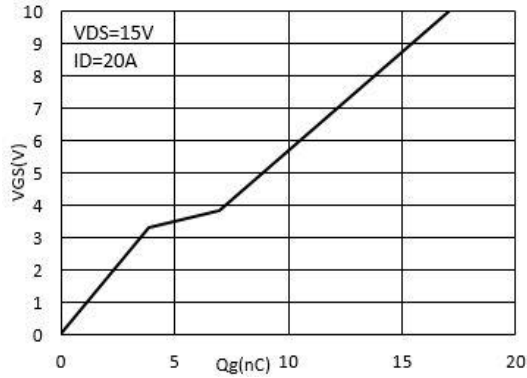


Figure 7: Gate-Charge Characteristics

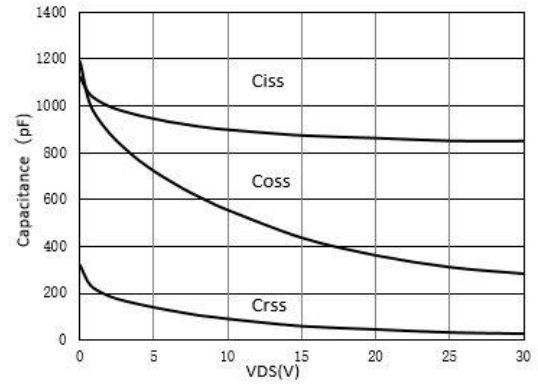
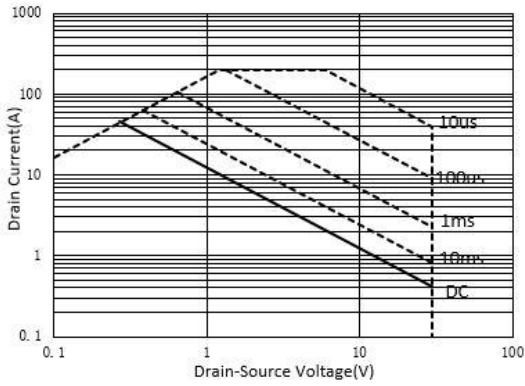
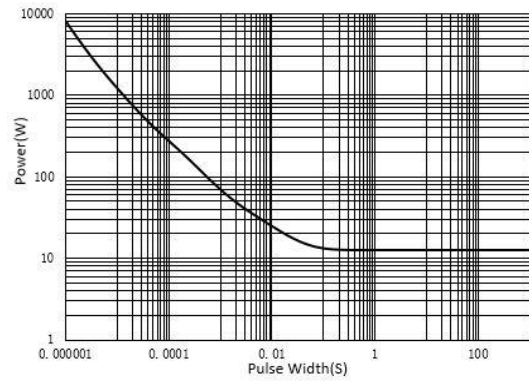
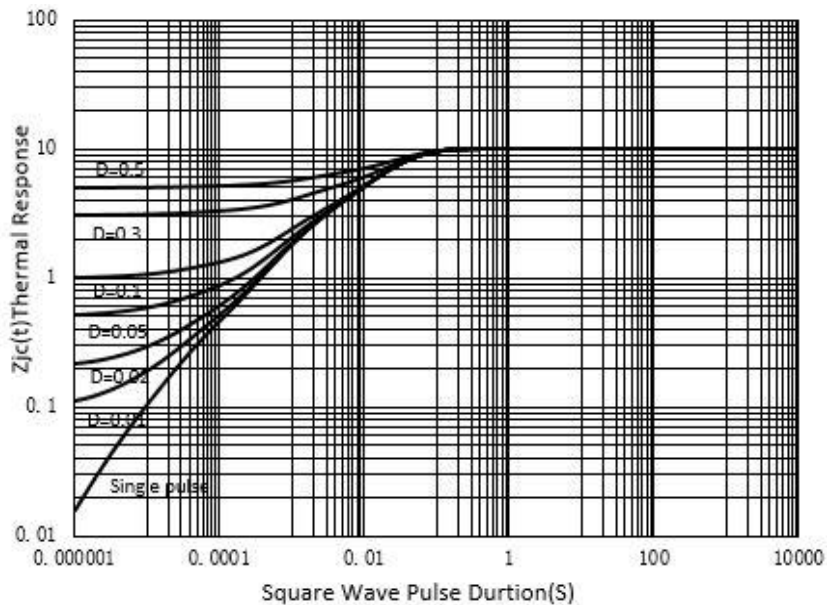
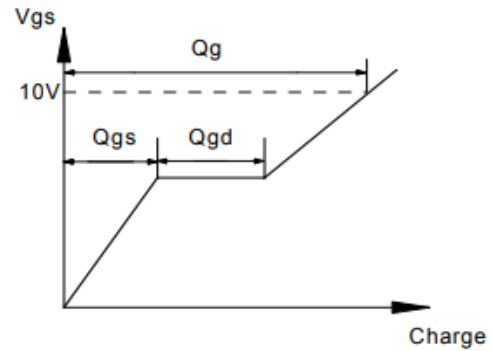
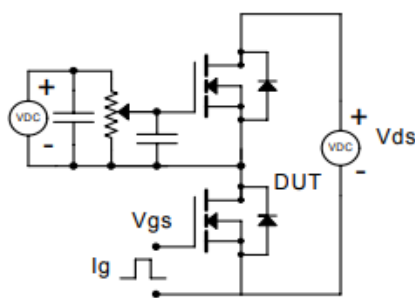


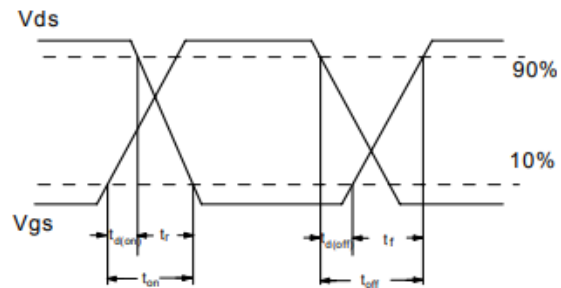
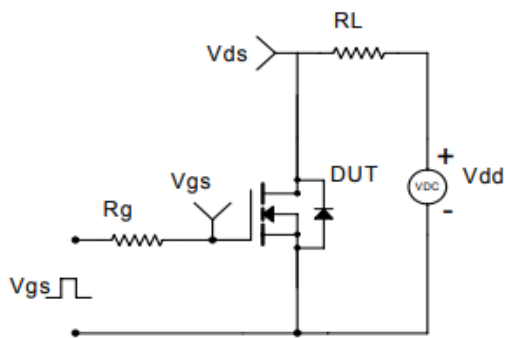
Figure 8: Capacitance Characteristics


 Figure 9: Maximum Forward Biased
Safe Operating Area

 Figure 10: Single Pulse Power Rating
Junction-to-Case


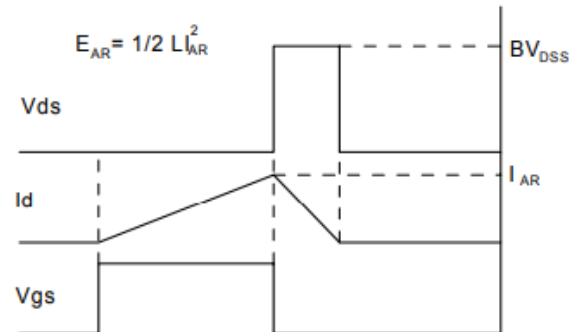
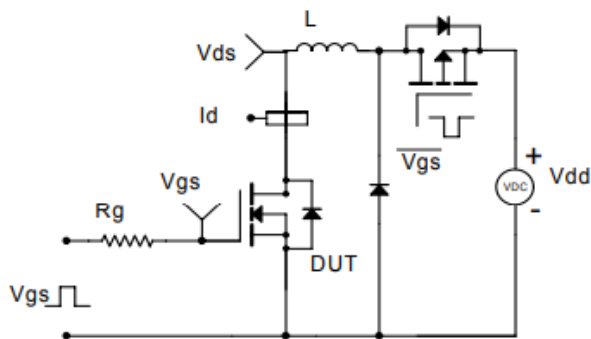
Gate Charge Test Circuit & Waveform



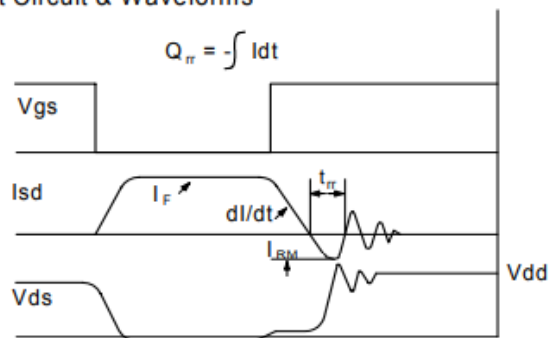
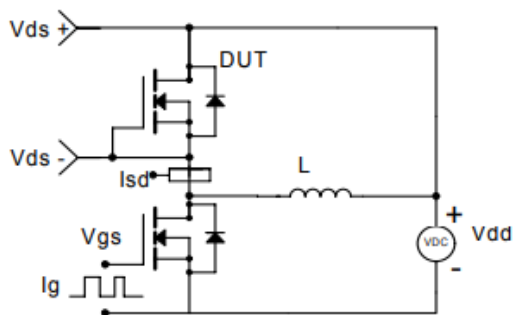
Resistive Switching Test Circuit & Waveforms

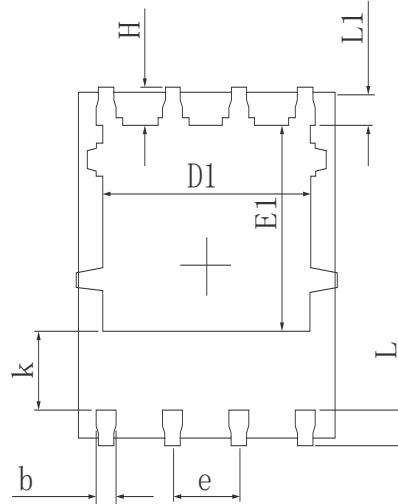
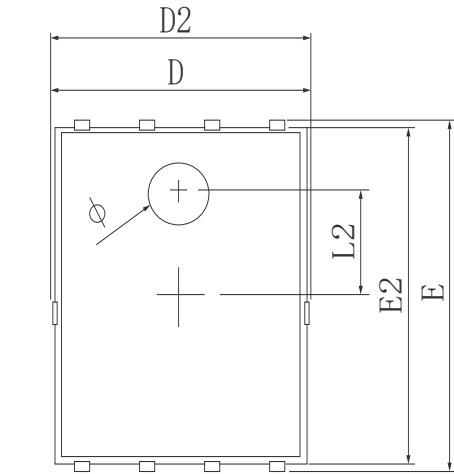


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

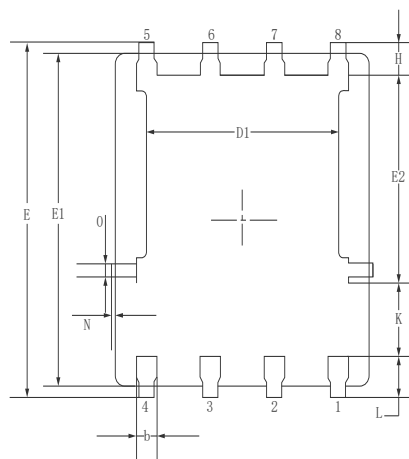
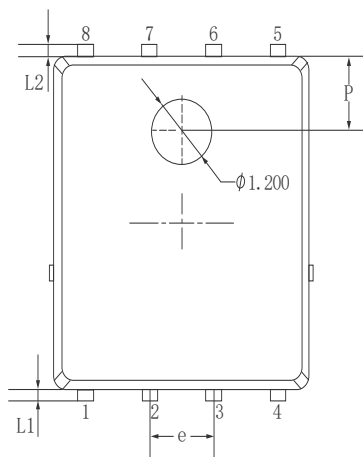
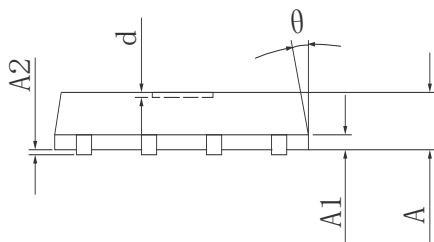


Diode Recovery Test Circuit & Waveforms

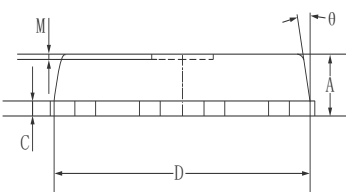


•Dimensions (PDFN5*6)


SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0°0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
Φ	1.100	1.200	1.300
d			0.100



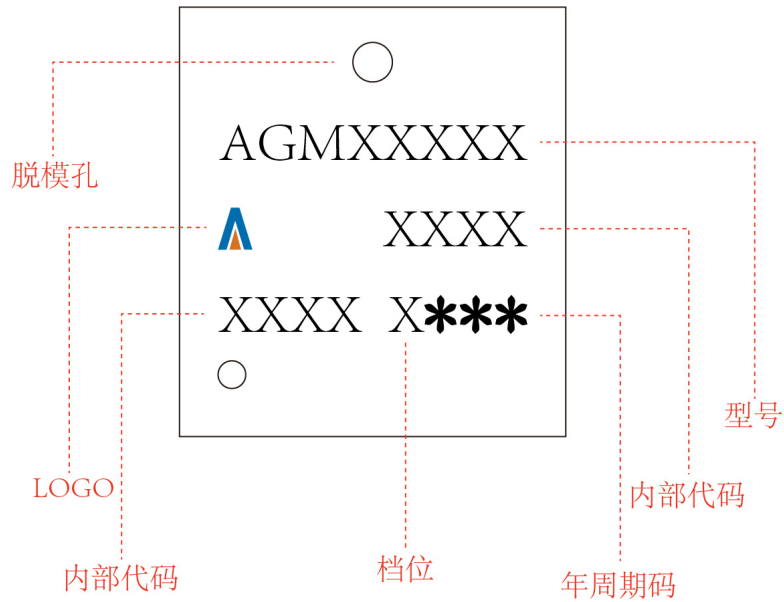
Symbol	Millimeters		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1	3.72	3.82	3.92
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		



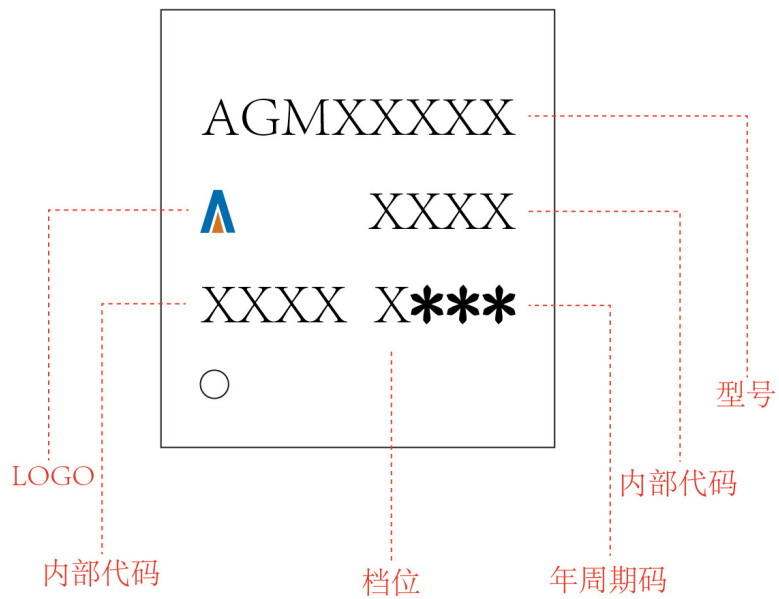
PDFN5*6

Marking Instructions:

Model1:



Model2:




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